

TM08G02MI6

N+P-Channel Enhancement Mode Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

N Channel

$V_{DS} = 20V, I_D = 8.0A$
 $R_{DS(ON)} = 17 m\Omega (typ.) @ V_{GS} = 4.5V$

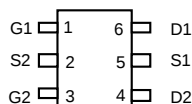
P Channel

$V_{DS} = -20V, I_D = -7.5A$
 $R_{DS(ON)} = 30 m\Omega (typ.) @ V_{GS} = -4.5V$

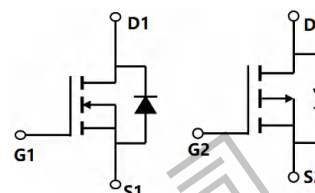
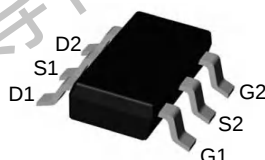
100% UIS Tested
100% R_g Tested



MI6:SOT-23-6L



Marking: 6G02L OR 20C03



Absolute Maximum Ratings: ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	N-Channel	P-Channel	Units
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	± 12	± 12	V
I_D	Continuous Drain Current- $T_C = 25^\circ C$	8	-7.5	A
	Continuous Drain Current- $T_C = 100^\circ C^1$	4.0	-2.6	
EAS	Single Pulse Avalanche Energy ³	72	59	mJ
I_{AS}	Avalanche Current	21	-19	A
P_D	Power Dissipation	1	1	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175		$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	70	$^\circ C/W$

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N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =3A	---	17	25	mΩ
		V _{GS} =2.5V, I _D =2A	---	21	30	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.4	0.75	1.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =16V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	10.5	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =3A	---	4.6	---	nC
Q _{gs}	Gate-Source Charge		---	0.7	---	
Q _{gd}	Gate-Drain Charge		---	1.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =10V, V _{GS} =4.5V, R _G =3.3Ω I _D =3A	---	1.6	---	ns
T _r	Rise Time		---	42	---	
T _{d(off)}	Turn-Off Delay Time		---	14	---	
T _f	Fall Time		---	7	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	310	---	pF
C _{oss}	Output Capacitance		---	49	---	
C _{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	8.0	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

TM08G02MI6

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P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-4.1A	---	30	38	mΩ
		V _{GS} =-2.5V, I _D =-3A	---	38	53	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.3	-0.65	-1	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-20V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	---	---	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-2A	---	8.8	---	nC
Q _{gs}	Gate-Source Charge		---	1.4	---	
Q _{gd}	Gate-Drain Charge		---	1.9	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =1Ω I _D =-3.3A	---	10	---	ns
T _r	Rise Time		---	32	---	
T _{d(off)}	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	51	---	
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	830	---	pF
C _{oss}	Output Capacitance		---	132	---	
C _{rss}	Reverse Transfer Capacitance		---	85	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-7.5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-4.1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

TM08G02MI6

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N-Channel Typical Characteristics

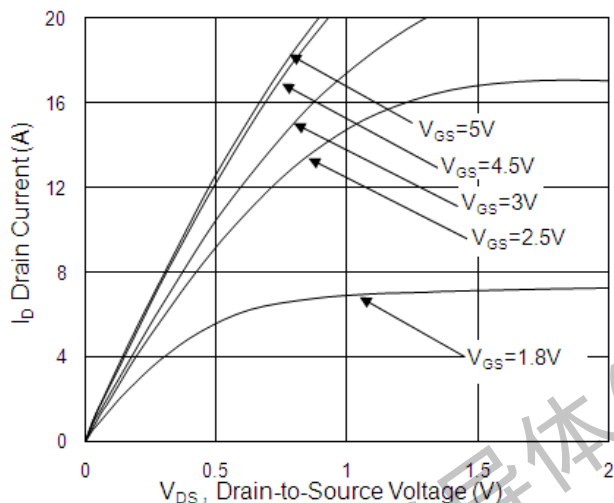


Fig.1 Typical Output Characteristics

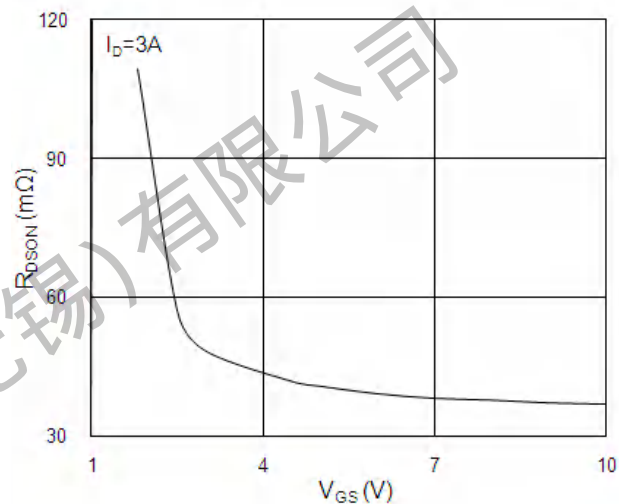


Fig.2 On-Resistance vs. Gate-Source Voltage

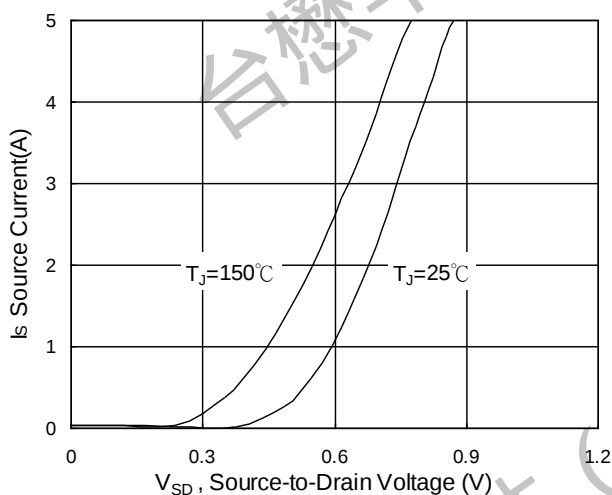


Fig.3 Forward Characteristics of Reverse

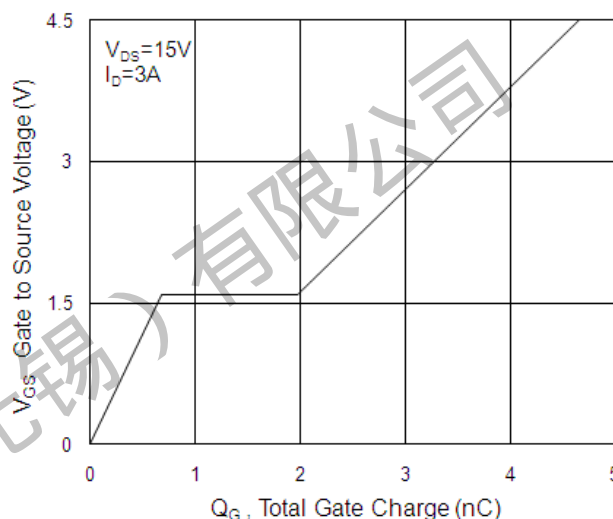


Fig.4 Gate-Charge Characteristics

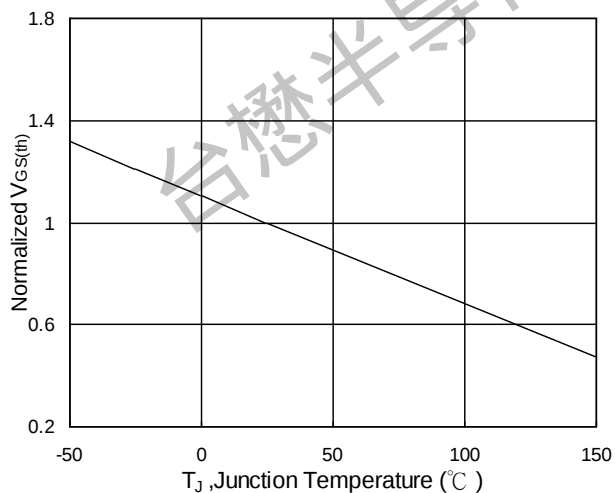


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

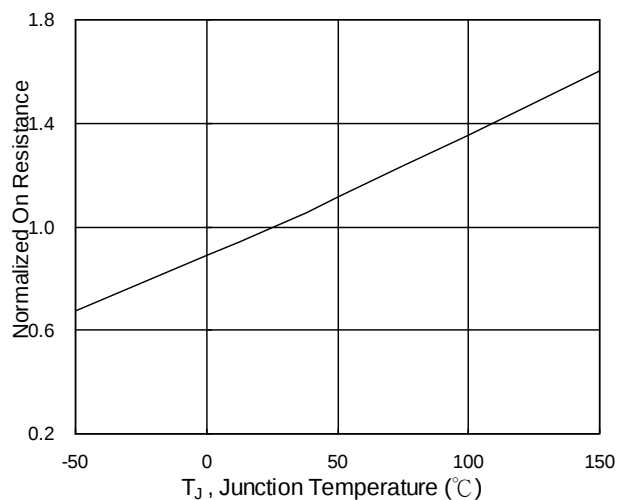


Fig.6 Normalized R vs. T

TM08G02MI6

N+P-Channel Enhancement Mode Mosfet

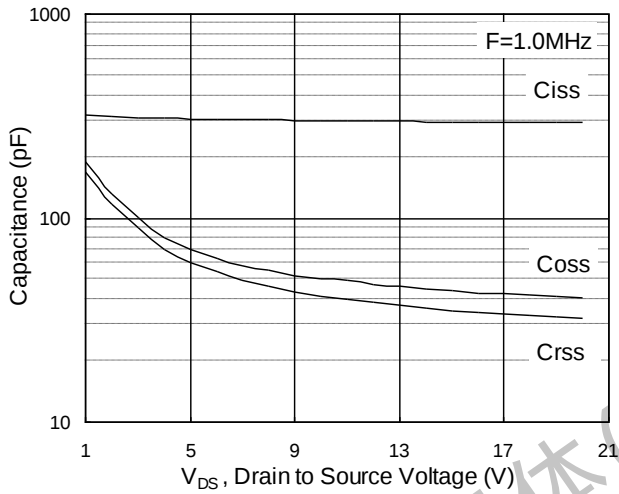


Fig.7 Capacitance

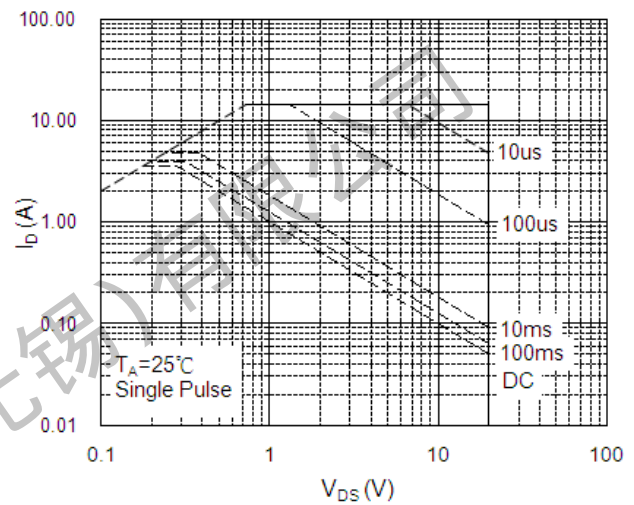


Fig.8 Safe Operating Area

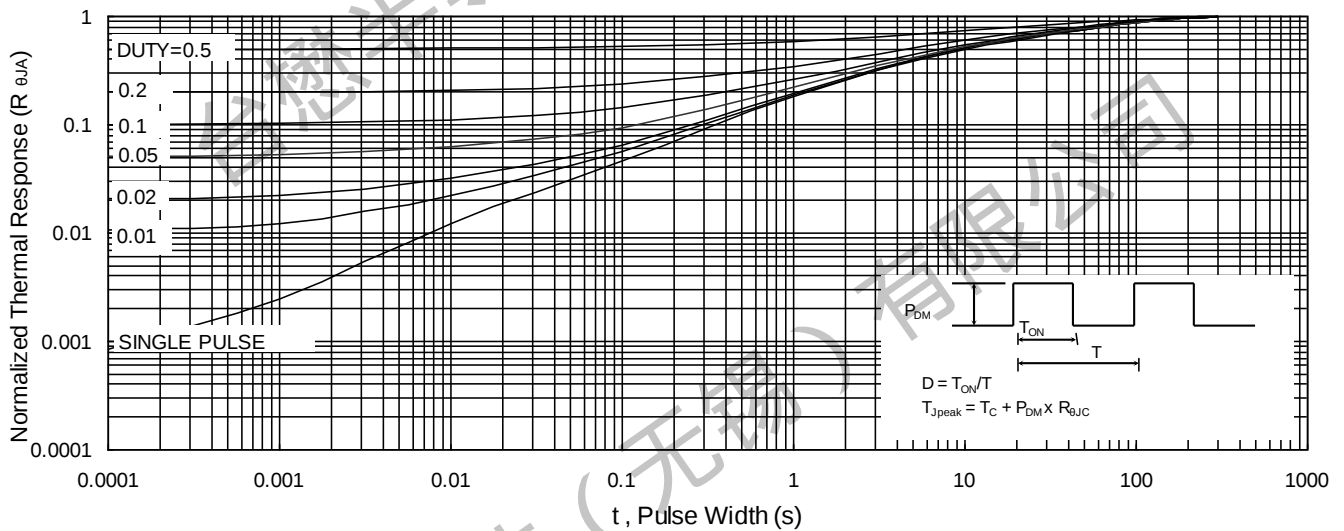


Fig.9 Normalized Maximum Transient Thermal Impedance

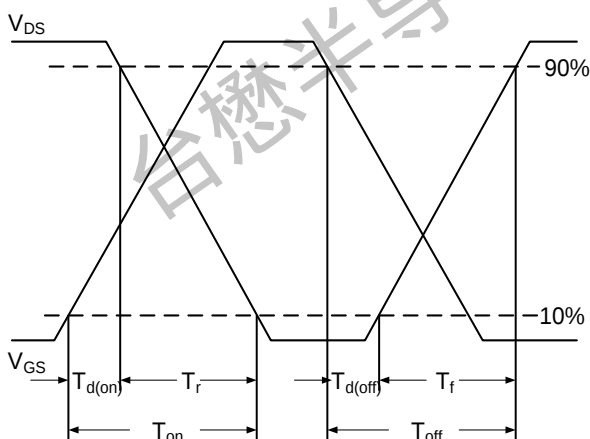


Fig.10 Switching Time Waveform

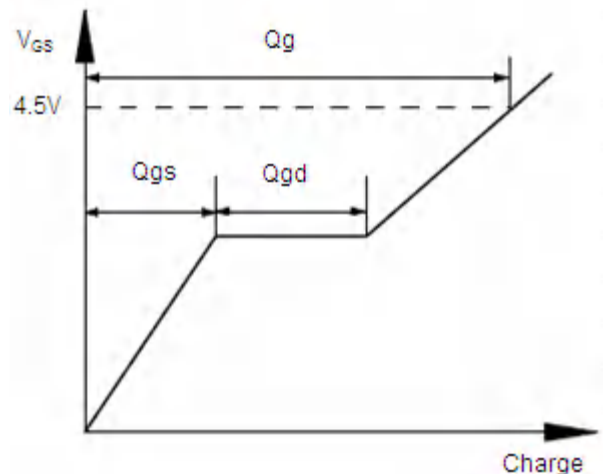


Fig.11 Gate Charge Waveform

P-Channel Typical Characteristics

Figure1: Output Characteristics

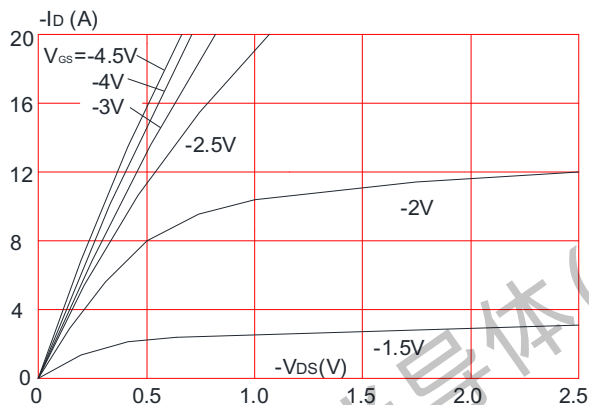


Figure 2: Typical Transfer Characteristics

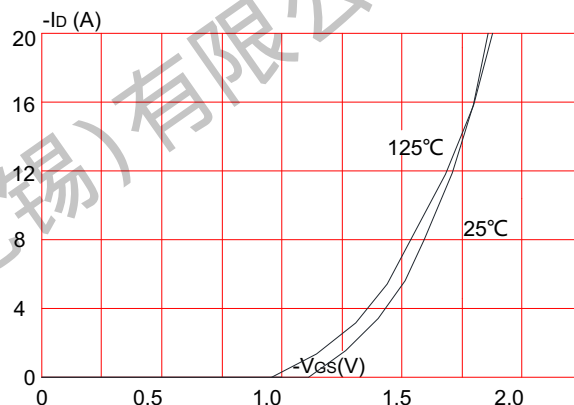


Figure 3: On-resistance vs. Drain Current

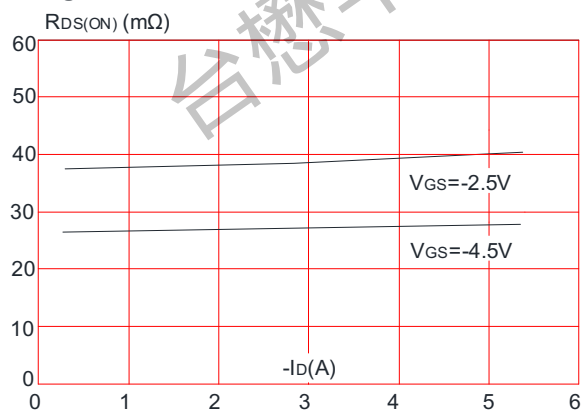


Figure 4: Body Diode Characteristics

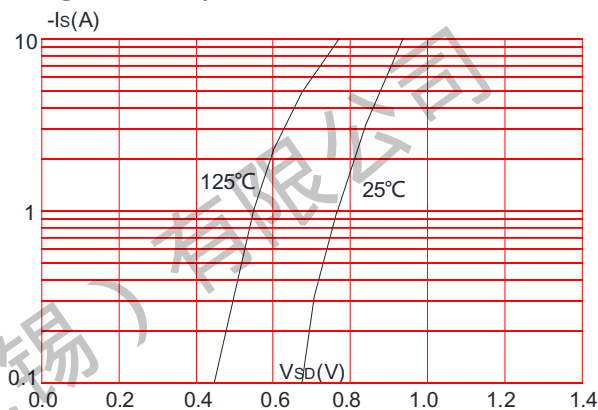


Figure 5: Gate Charge Characteristics

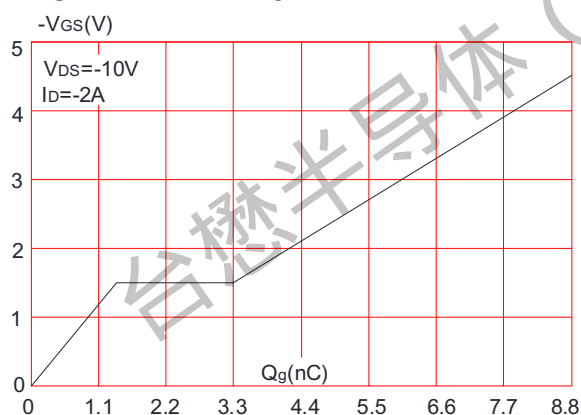
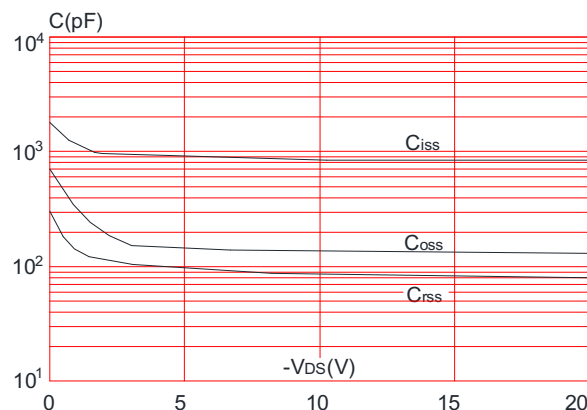


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

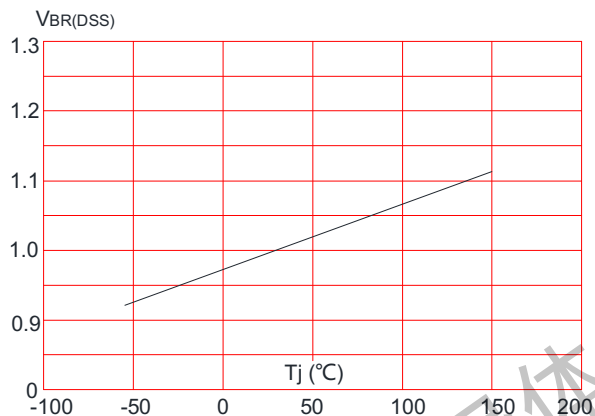


Figure 8: Normalized on Resistance vs. Junction Temperature

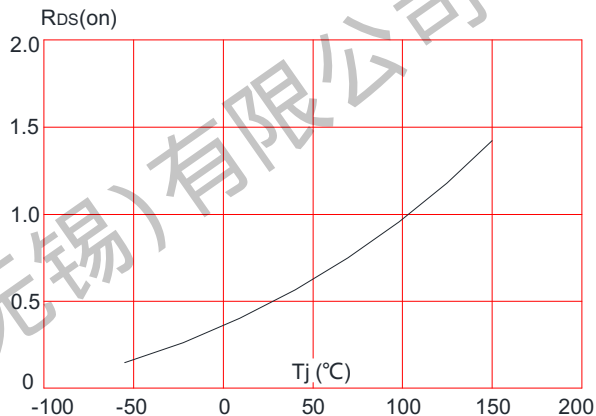


Figure 9: Maximum Safe Operating Area

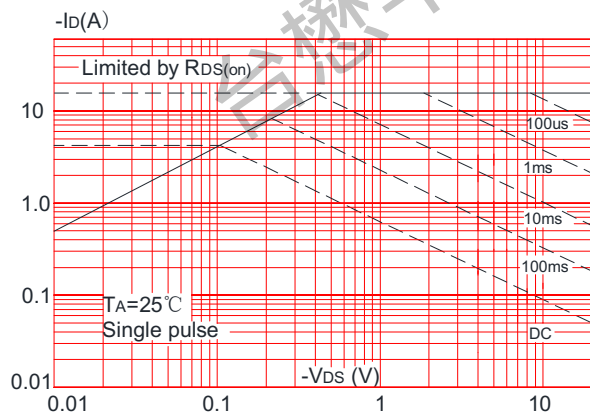


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

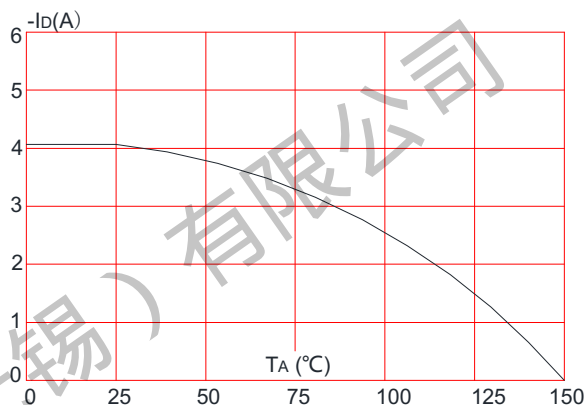
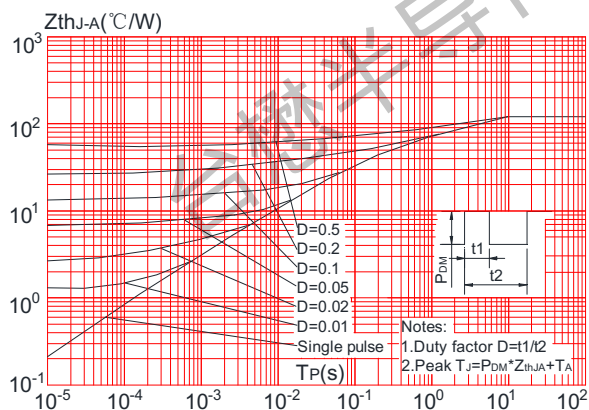


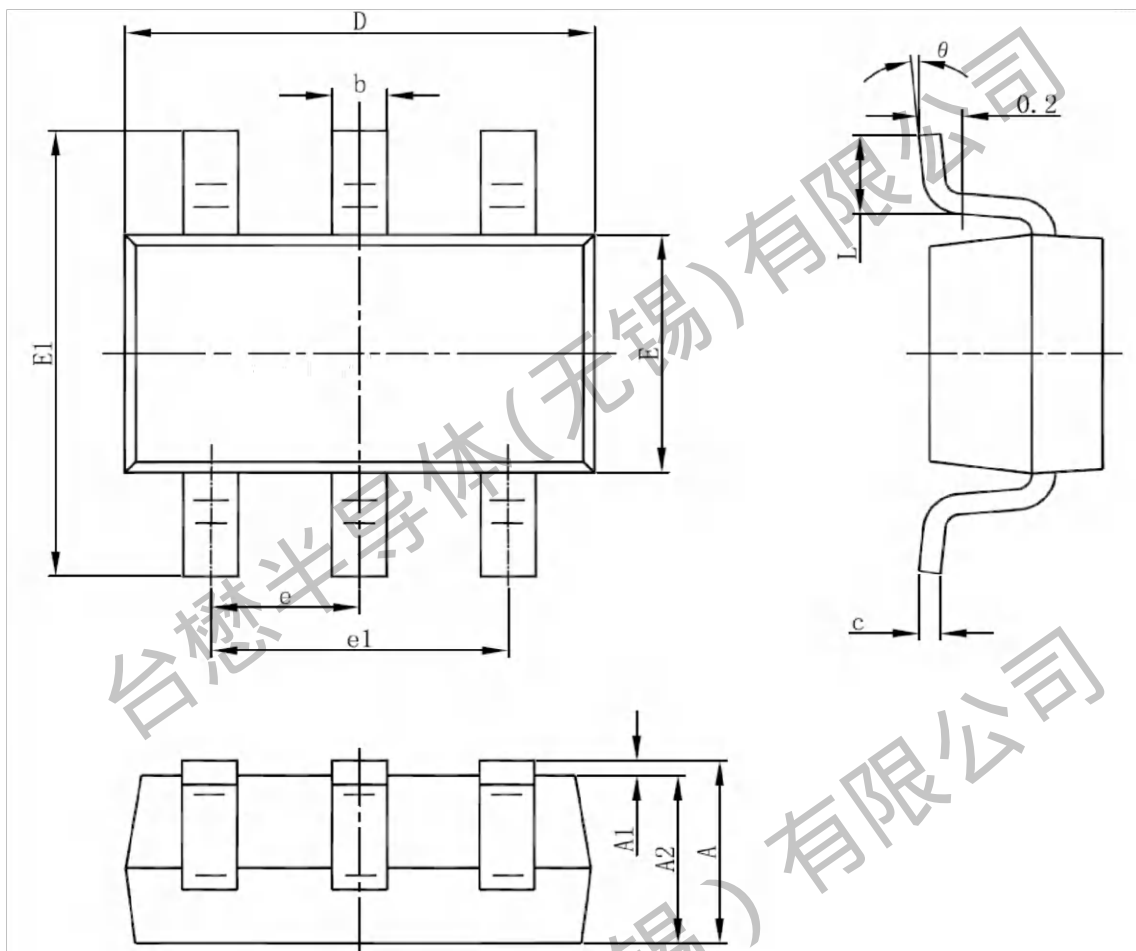
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



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Package Mechanical Data:SOT-23-6L

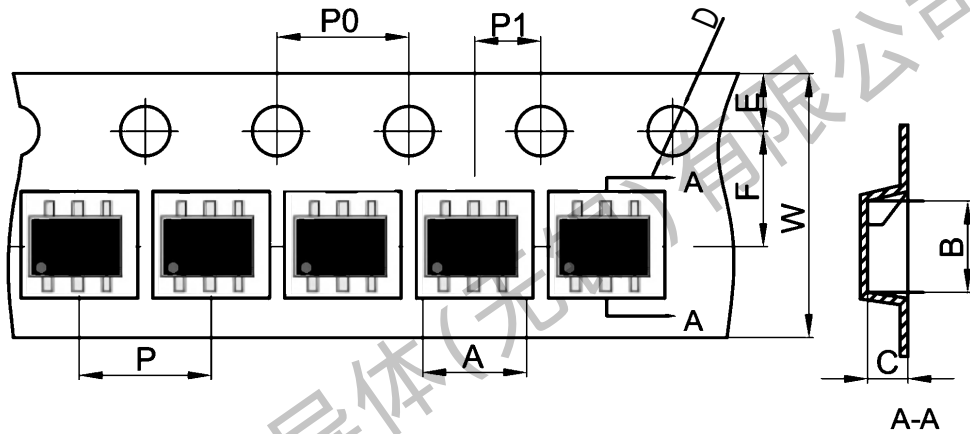


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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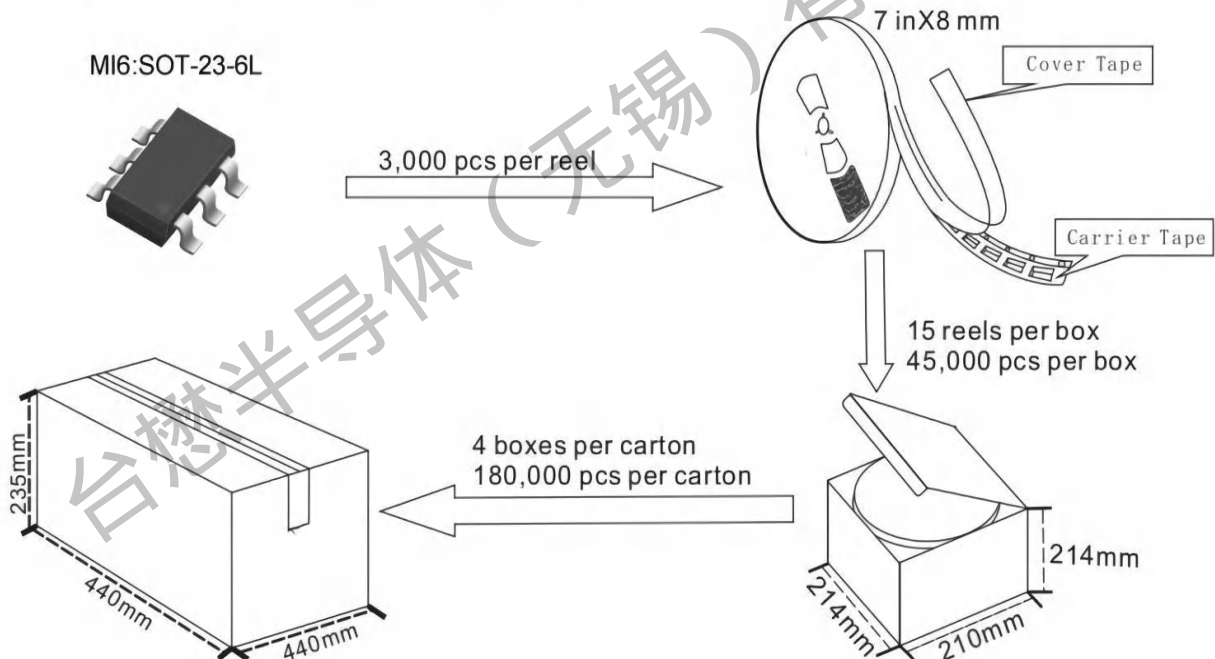
SOT-23-6L Embossed Carrier Tape



Dimensions are in millimeter										
Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23-6L	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-6L Packing

The method of packaging and dimension are shown as below figure. (Dimension in mm)



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Revision history:

Date	Rev	Description	Page
2023.06.22	23.06	Original	